

FEATURES

- 320nm UVB response
- Visible & NIR blind
- Photovoltaic operation
- High shunt resistance

DESCRIPTION

The **PDU-G102B** is a GaN UV photodiode with a spectral range from 200nm to 320nm and is ideal for UVB sensing applications available in a TO-46 can package.

APPLICATIONS

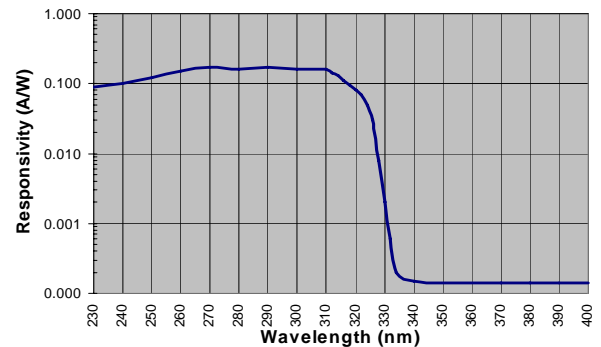
- UVB power meters
- Sun dosimeters
- UV epoxy curing
- UV instrumentation

ABSOLUTE MAXIMUM RATING (TA)= 23°C UNLESS OTHERWISE NOTED

SYMBOL	PARAMETER	MIN	MAX	UNITS
V _{BR}	Reverse Voltage		5	V
T _{STG}	Storage Temperature	-40	+90	°C
T _O	Operating Temperature	-30	+85	°C
T _S	Soldering Temperature*		+260	°C

* 1/16 inch from case for 3 seconds max.

SPECTRAL RESPONSE



ELECTRO-OPTICAL CHARACTERISTICS RATING (TA)= 23°C UNLESS OTHERWISE NOTED

SYMBOL	CHARACTERISTIC	TEST CONDITIONS	MIN	TYP	MAX	UNITS
I _{SC}	Short Circuit Current	UVI = 1		1		nA
I _D	Dark Current	V _R = 1V		50	100	µA
R _{SH}	Shunt Resistance	V _R = 10 mV	0.45	1		GΩ
C _J	Junction Capacitance	V _R = 0V, f = 1 MHz		24		pF
λ range	Spectral Application Range	Spot Scan	200		320	nm
R	Responsivity	λ = 350nm V, V _R = 0 V		0.10		A/W
V _{BR}	Breakdown Voltage	I = 1µA		10		V
t _r	Response Time**	RL = 1KΩ, V _R = 1V		10	15	nS

**Response time of 10% to 90% is specified at 660nm wavelength light.

Information in this technical datasheet is believed to be correct and reliable. However, no responsibility is assumed for possible inaccuracies or omission. Specifications are subject to change without notice.